



## Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+NPN)

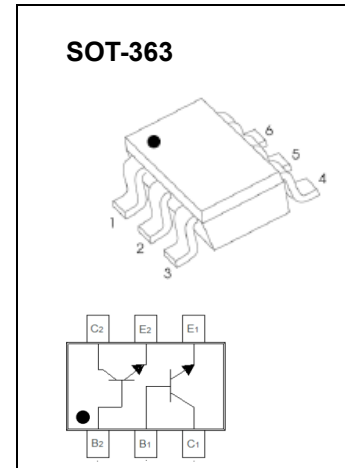
### FEATURES

- Epitaxial planar die construction
- Ideal for low power amplification and switching

MARKING:K4A

MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	0.2	A
$P_C$	Collector Power Dissipation	0.2	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=30\text{V}, I_E=0$			0.05	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.05	$\mu\text{A}$
Collector cut-off current	$I_{CEX}$	$V_{CE}=30\text{V}, V_{BE(off)}=3\text{V}$			0.05	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40			
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=1\text{mA}$	70			
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60			
	$h_{FE(5)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.2	V
	$V_{CE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=10\text{mA}, I_B=1\text{mA}$	0.65		0.85	V
	$V_{BE(sat)2}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.95	V
Transition frequency	$f_T$	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=5\text{V}, I_E=0, f=1\text{MHz}$			4	pF
Noise figure	NF	$V_{CE}=5\text{V}, I_C=0.1\text{mA}, f=1\text{kHz}, R_S=1\text{K}\Omega$			5	dB
Delay time	$t_d$	$V_{CC}=3\text{V}, V_{BE(off)}=-0.5\text{V}$			35	nS
Rise time	$t_r$	$I_C=10\text{mA}, I_{B1}=-I_{B2}=1\text{mA}$			35	nS
Storage time	$t_s$	$V_{CC}=3\text{V}, I_C=10\text{mA}$			200	nS
Fall time	$t_f$	$I_{B1}=-I_{B2}=1\text{mA}$			50	nS

### TYPICAL TRANSIENT CHARACTERISTICS

—  $T_J = 25^\circ\text{C}$   
- -  $T_J = 125^\circ\text{C}$

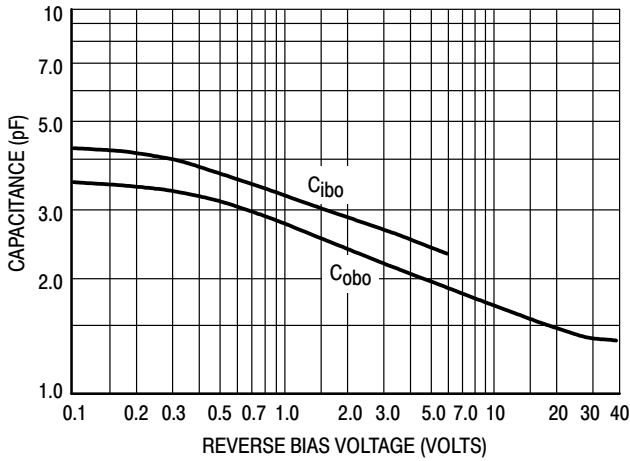


Figure 3. Capacitance

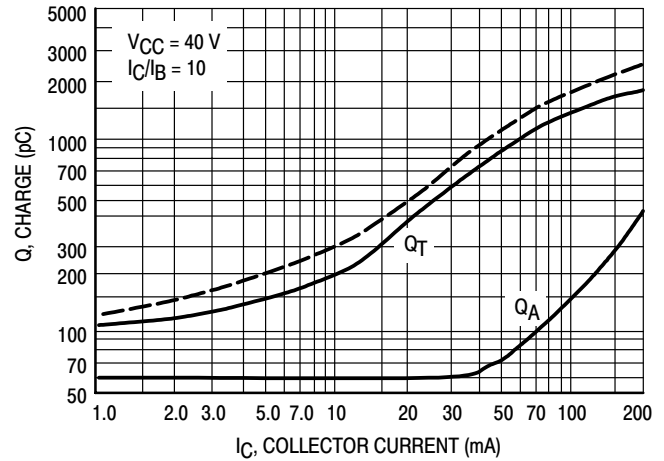


Figure 4. Charge Data

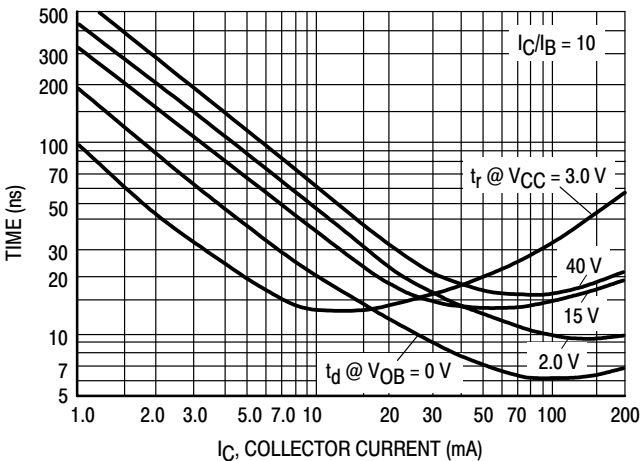


Figure 5. Turn-On Time

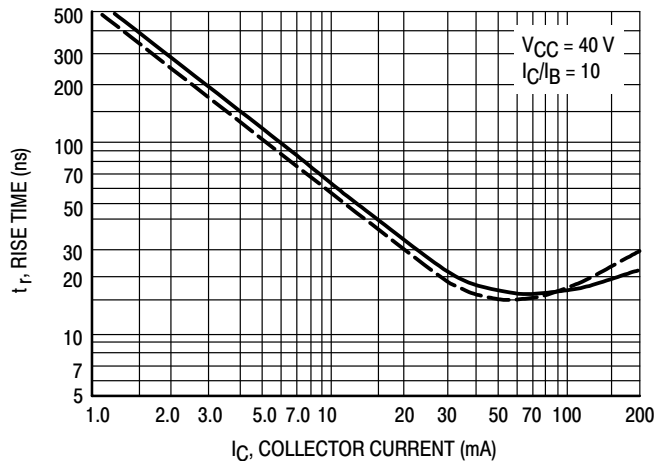


Figure 6. Rise Time

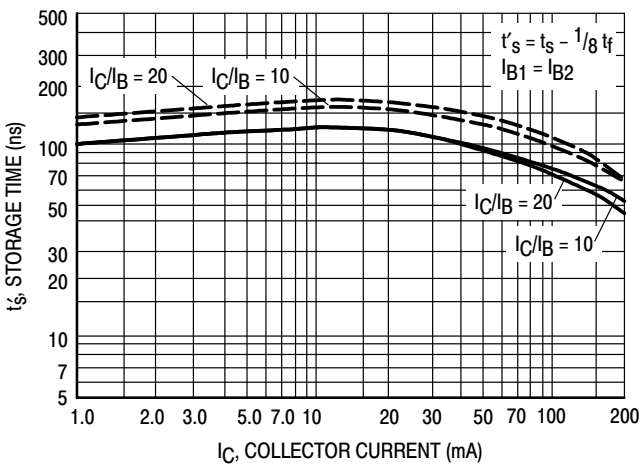


Figure 7. Storage Time

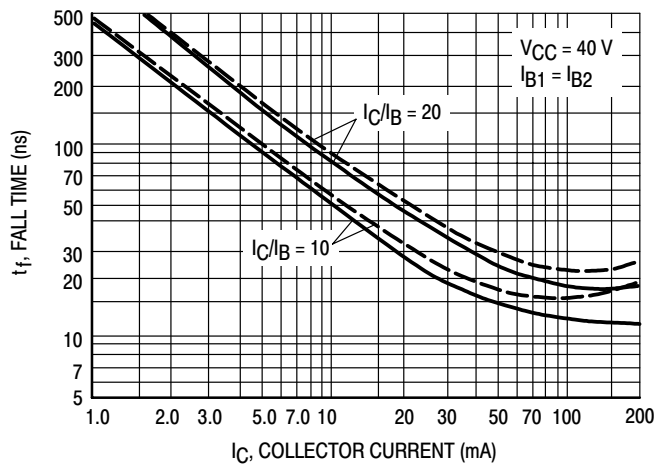


Figure 8. Fall Time



TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS  
NOISE FIGURE VARIATIONS

(V<sub>CE</sub> = 5.0 Vdc, T<sub>A</sub> = 25°C, Bandwidth = 1.0 Hz)

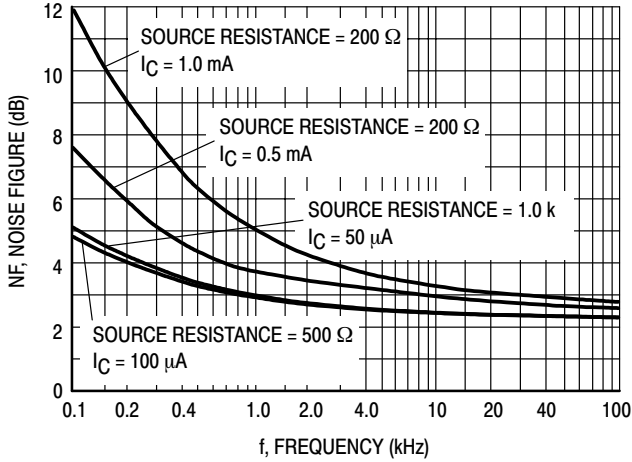


Figure 9. Noise Figure

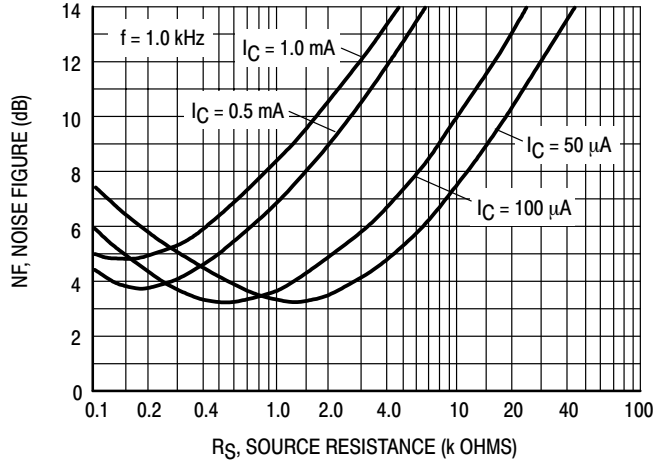


Figure 10. Noise Figure

h PARAMETERS

(V<sub>CE</sub> = 10 Vdc, f = 1.0 kHz, T<sub>A</sub> = 25°C)

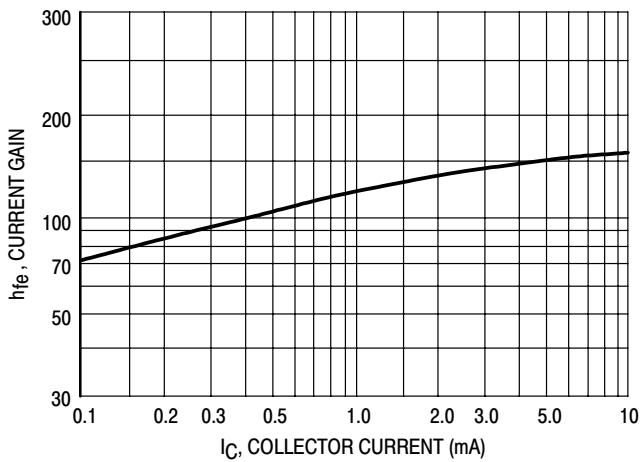


Figure 11. Current Gain

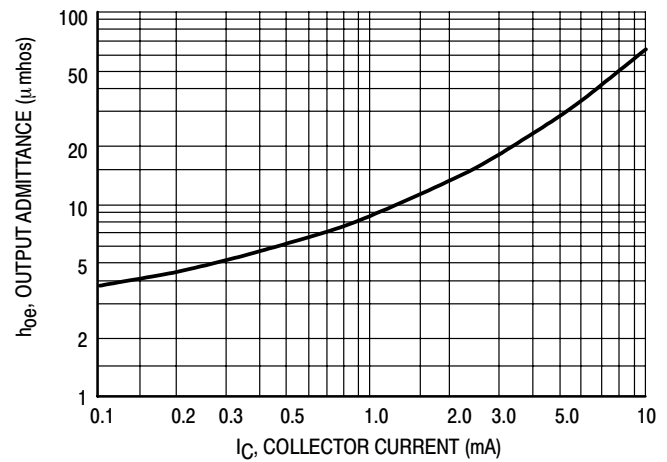


Figure 12. Output Admittance

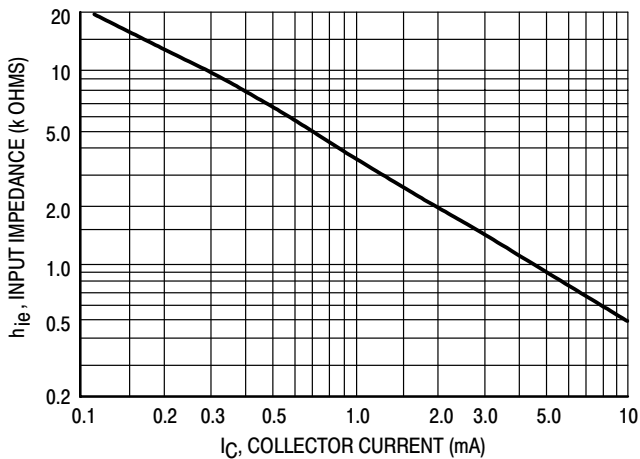


Figure 13. Input Impedance

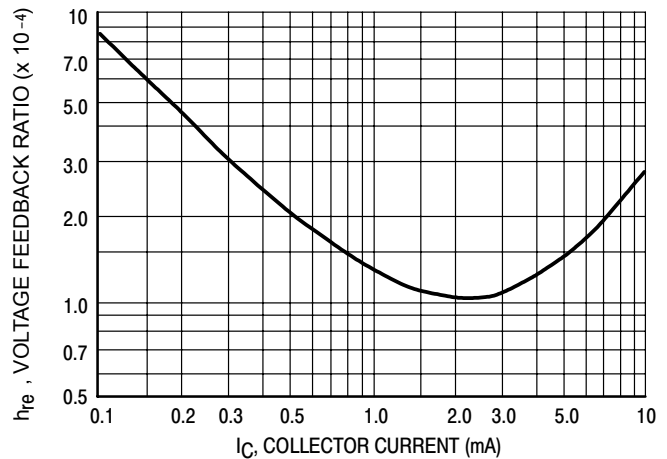


Figure 14. Voltage Feedback Ratio



### TYPICAL STATIC CHARACTERISTICS

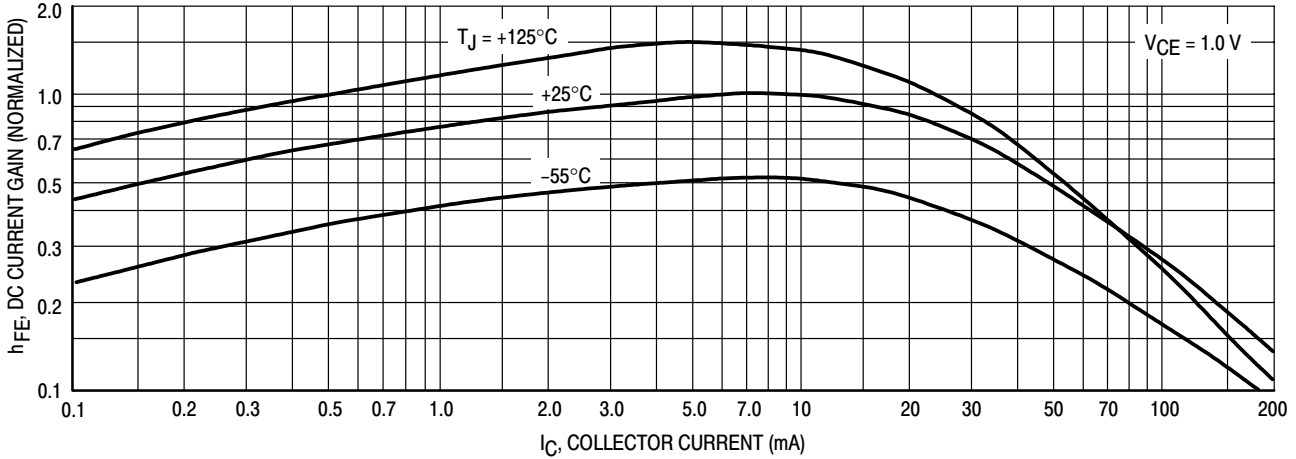


Figure 15. DC Current Gain

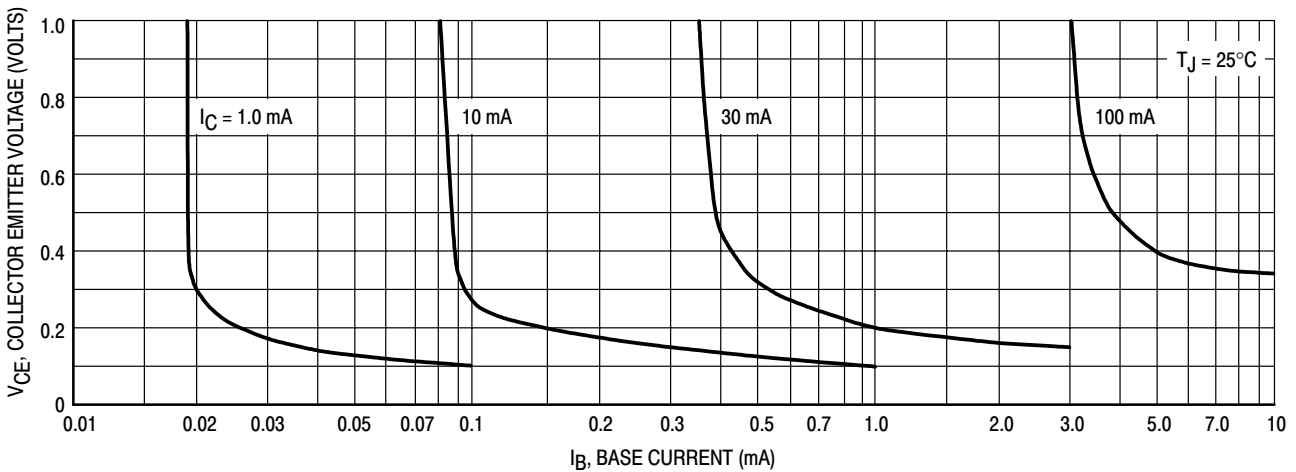


Figure 16. Collector Saturation Region

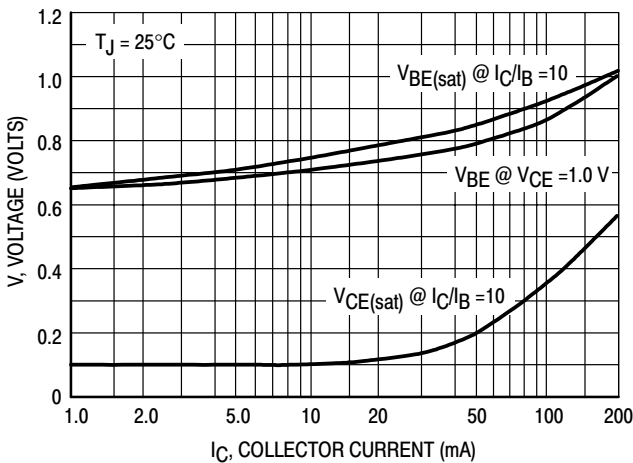


Figure 17. "ON" Voltages

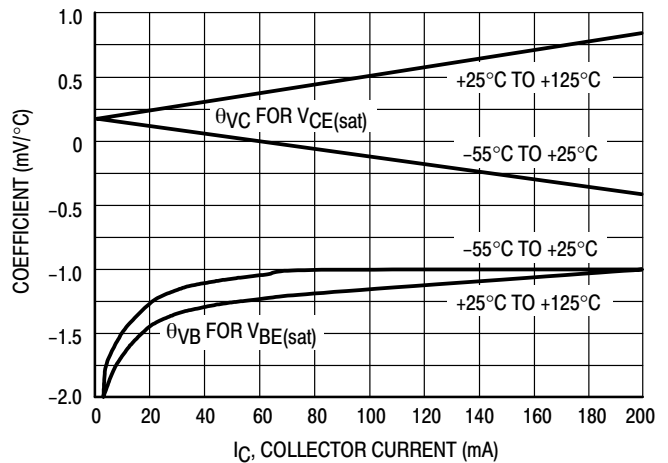
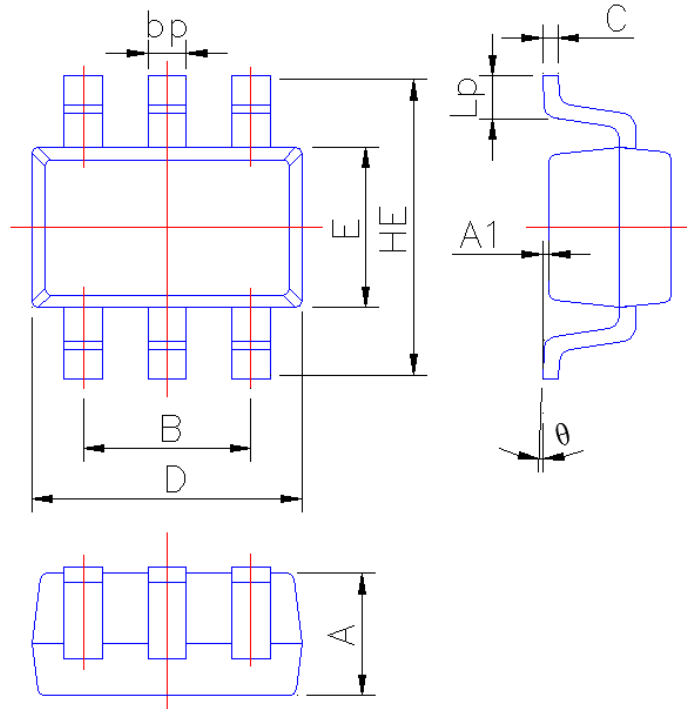


Figure 18. Temperature Coefficients



## SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
$\theta$	0°	6°